Ordering number : ENA1315A

EMH2412

N-Channel Power MOSFET
24V, 6A, 27mΩ, Dual EMH8

ON Semiconductor®
http://onsemi.com

Features

- Low ON-resistance
- Best suited for LiB charging and discharging switch
- Common-drain type
- 2.5V drive
- Halogen free compliance
- Protection diode in

Specifications

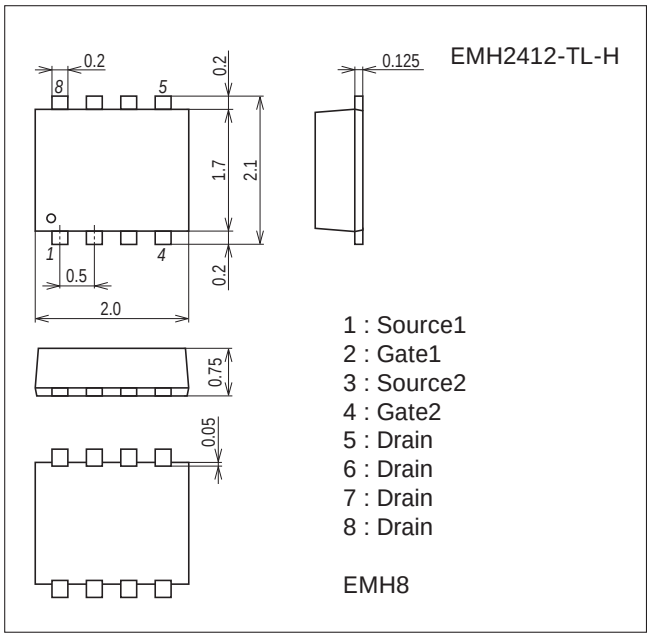
Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		24	V
Gate-to-Source Voltage	V_{GSS}		±12	V
Drain Current (DC)	I_D		6	A
Drain Current (Pulse)	I_{DP}	PW≤10μs, duty cycle≤1%	60	A
Allowable Power Dissipation	P_D	When mounted on ceramic substrate (900mm²×0.8mm) 1unit	1.3	W
Total Dissipation	P_T	When mounted on ceramic substrate (900mm²×0.8mm)	1.4	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		−55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Package Dimensions

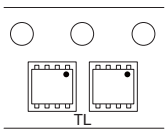
unit : mm (typ)
7045-006



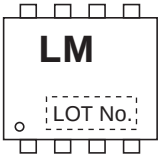
Product & Package Information

- Package : EMH8
- JEITA, JEDEC : -
- Minimum Packing Quantity : 3,000 pcs./reel

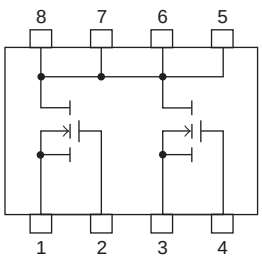
Taping Type : TL



Marking



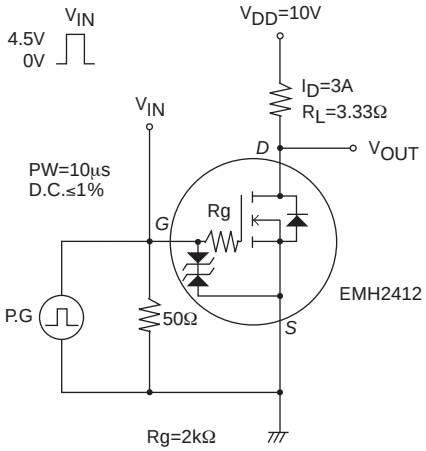
Electrical Connection



Electrical Characteristics at Ta=25°C

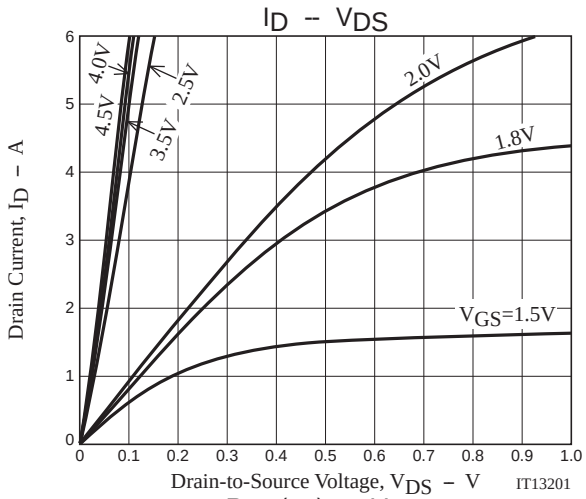
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D=1mA, V_{GS}=0V	24			V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS}=20V, V_{GS}=0V			−1	μA
Gate-to-Source Leakage Current	I_{GSS}	V_{GS}=±8V, V_{DS}=0V			±10	μA
Cutoff Voltage	V_{GS}(off)	V_{DS}=10V, I_D=1mA	0.5		1.3	V
Forward Transfer Admittance	| yfs |	V_{DS}=10V, I_D=3A	2.8	4.8		S
Static Drain-to-Source On-State Resistance	R_{DS}(on)1	I_D=3A, V_{GS}=4.5V	16	21	27	mΩ
	R_{DS}(on)2	I_D=3A, V_{GS}=4V	17	22	29	mΩ
	R_{DS}(on)3	I_D=3A, V_{GS}=3.1V	18	25	34	mΩ
	R_{DS}(on)4	I_D=1.5A, V_{GS}=2.5V	21	30	42	mΩ
Turn-ON Delay Time	t_{d}(on)	See specified Test Circuit.		310		ns
Rise Time	t_r			1020		ns
Turn-OFF Delay Time	t_{d}(off)			3000		ns
Fall Time	t_f			2250		ns
Total Gate Charge	Qg	V_{DS}=10V, V_{GS}=4.5V, I_D=6A		6.3		nC
Gate-to-Source Charge	Qgs			0.83		nC
Gate-to-Drain “Miller” Charge	Qgd			1.9		nC
Diode Forward Voltage	V_{SD}	I_S=6A, V_{GS}=0V		0.8	1.2	V

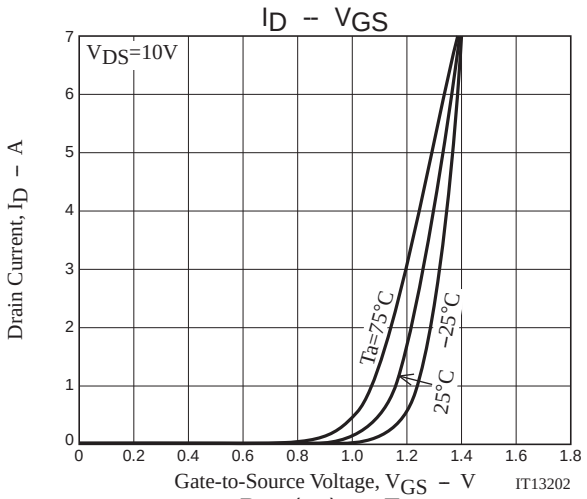
Switching Time Test Circuit

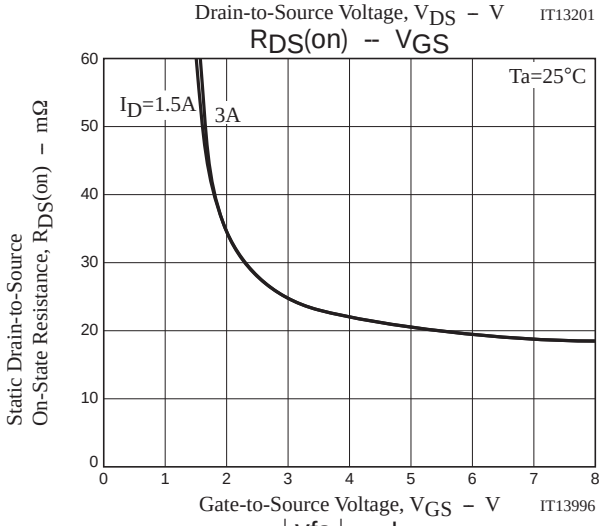


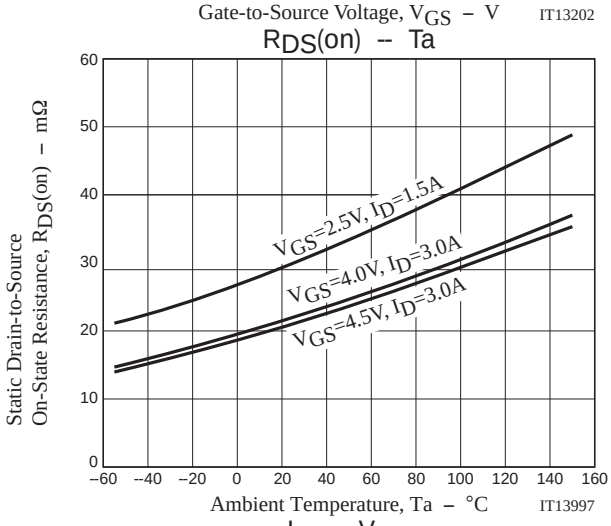
Ordering Information

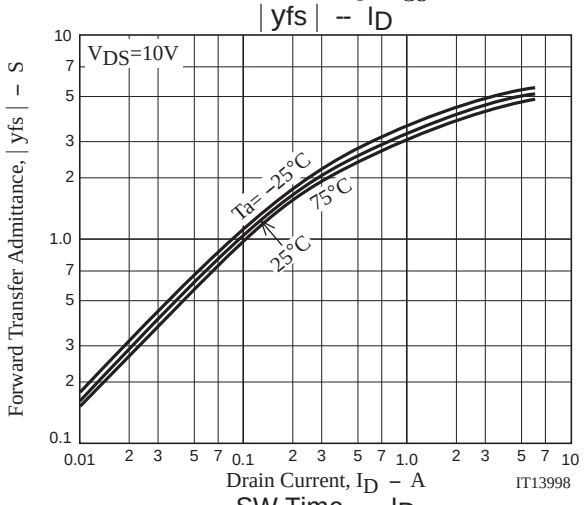
Device	Package	Shipping	memo
EMH2412-TL-H	EMH8	3,000pcs./reel	Pb Free and Halogen Free

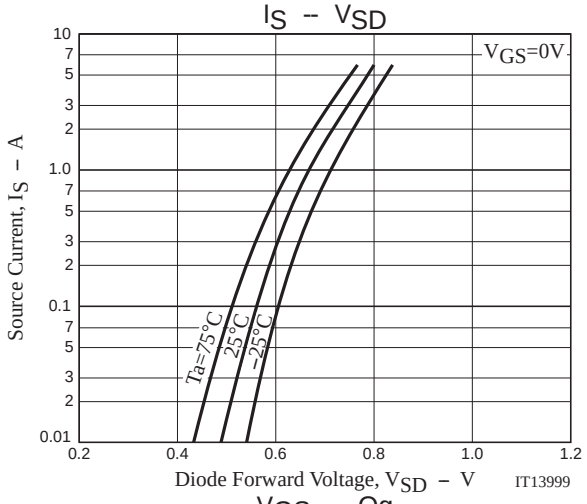


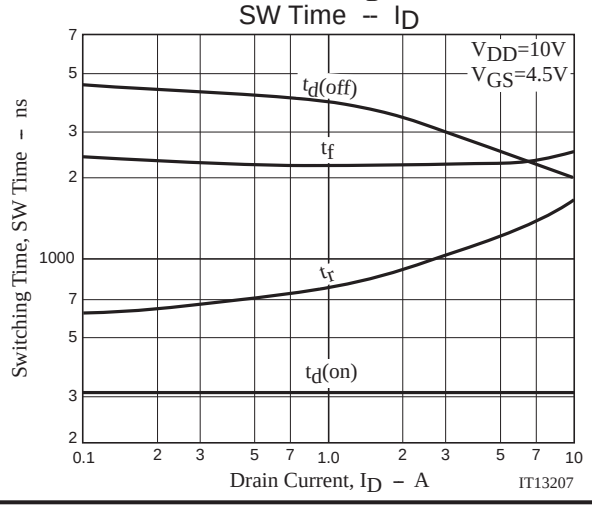


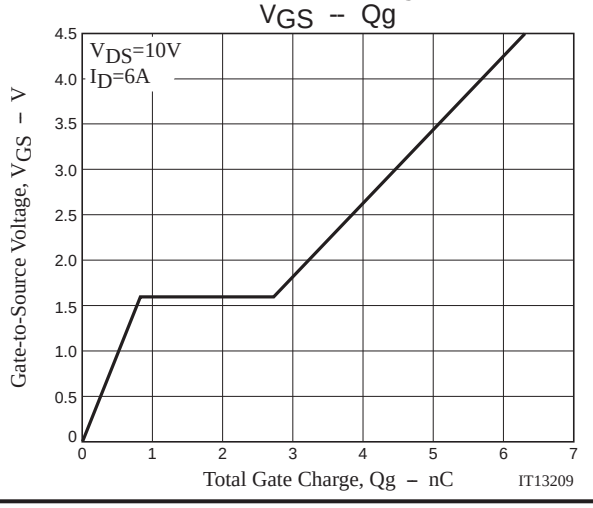


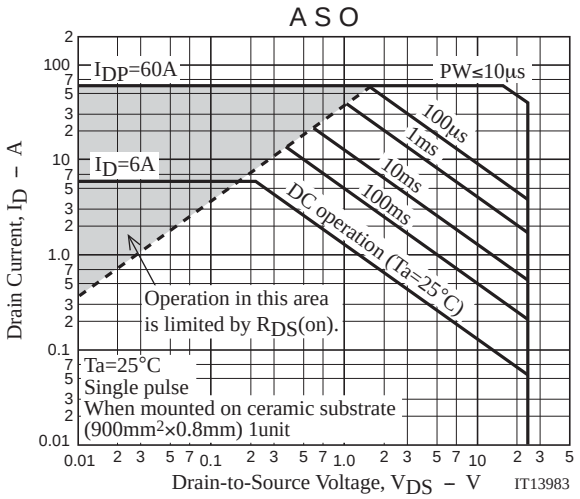


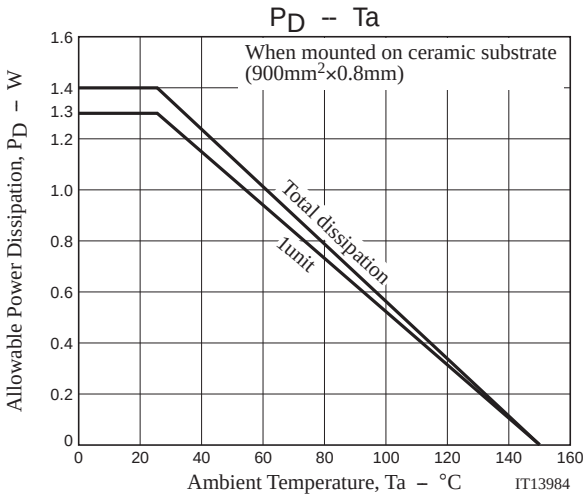












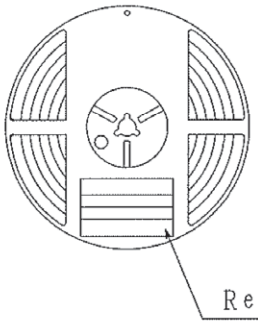
Embossed Taping Specification

EMH2412-TL-H

1. Packing Format

Package Name	Carrier Tape Type	Maximum Number of devices contained (pcs)			Packing format	
		Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)
EMH8	MCP4	3,000	15,000	90,000	5 reels contained Dimensions:mm (external) 183×72×185	6 inner boxes contained Dimensions:mm (external) 440×195×210

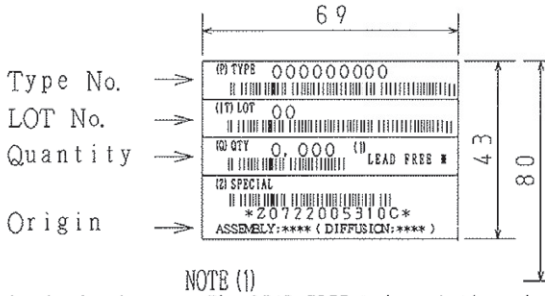
Packing method



Reel label

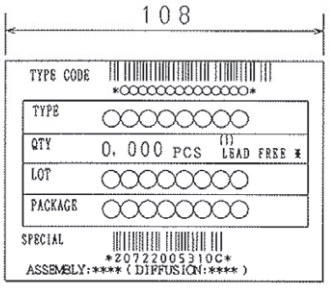
Reel label, Inner box label

(unit:mm)



Outer box label

It is a label at the time of factory shipments. The form of a label may change in physical distribution process.



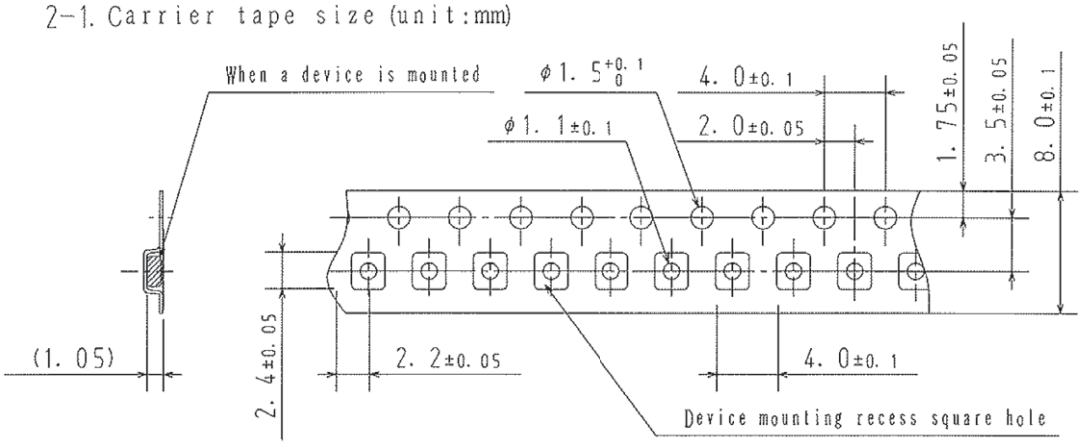
NOTE (1)

The LEAD FREE ※ description shows that the surface treatment of the terminal is lead free.

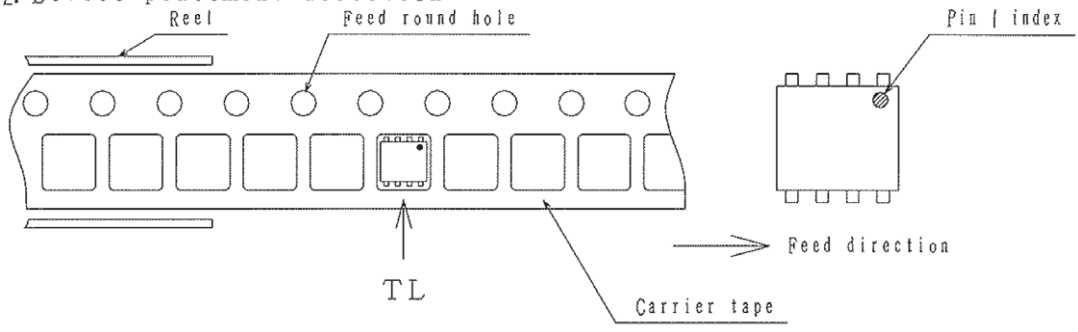
Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A
LEAD FREE 4	JEITA Phase 3

2. Taping configuration

2-1. Carrier tape size (unit:mm)



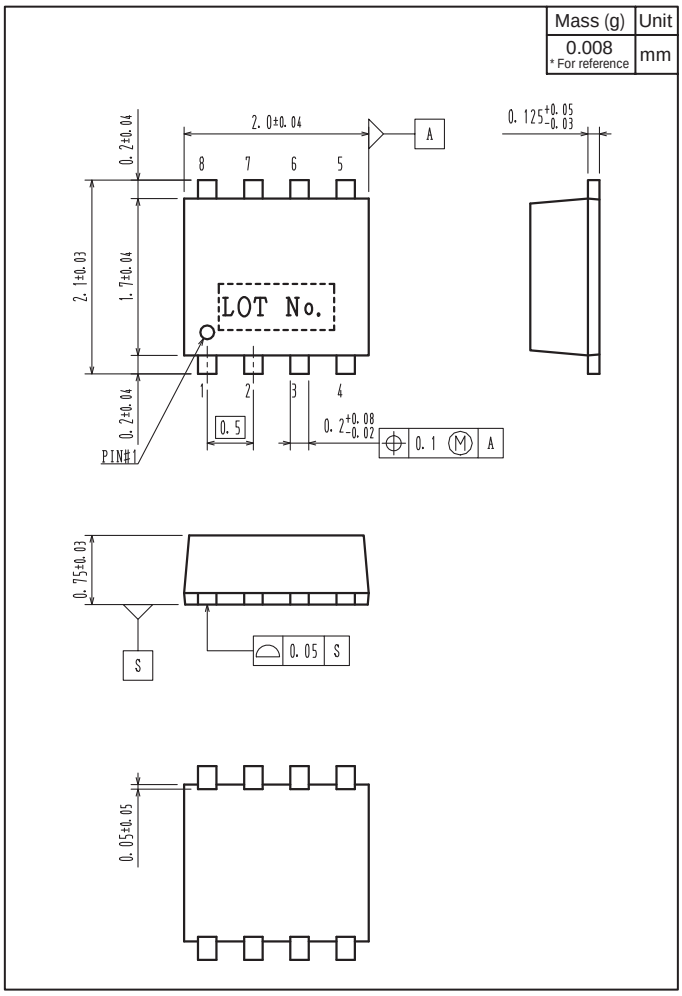
2-2. Device placement direction



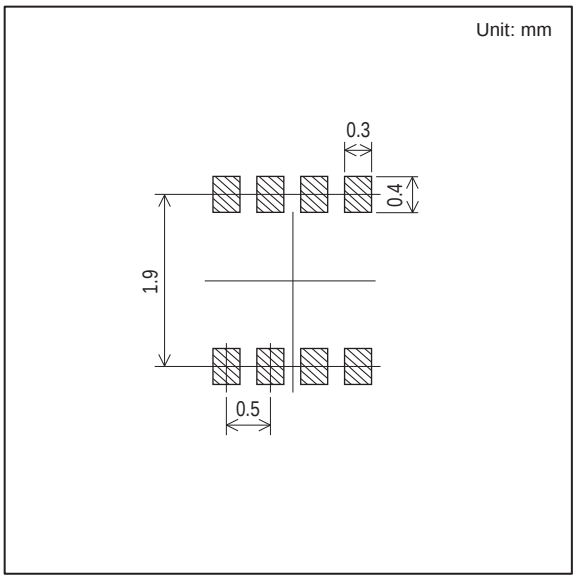
Those with pin 1 index on the feed hole side·····TL

Outline Drawing

EMH2412-TL-H



Land Pattern Example



Note on usage : Since the EMH2412 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.